Abstract Submitted
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Diffusion of Copper through Ti overlayer[1] BRITT LONG, A CHOURASIA, Texas AM University-Commerce — The Cu/Ti interface has been characterized by x-ray photoelectron spectroscopy and resistivity measurements. Thin films of copper were deposited on titanium substrates by e-beam method. The thickness of the Ti film was kept at 500 Å. The interface was annealed at temperatures of 100, 200, and 300C. The Ti 2p and Cu 2p regions were analyzed by XPS. The diffusivity of copper through titanium has been investigated.

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